

METHODS FOR FORMING A SILICON OXIDE LAYER OVER A SUBSTRATE

CROSS-REFERENCES TO RELATED APPLICATIONS

5 [0001] This application is related to co-assigned U.S. Provisional Patent Application No. 60/803,499 to Lubomirsky *et al.*, filed May 30, 2006, and titled "PROCESS CHAMBER FOR DIELECTRIC GAPFILL." This application is related to co-assigned U.S. Patent No. 6,387,207 to Janakiraman *et al.*, issued May 14, 2002, and titled "INTEGRATION OF REMOTE PLASMA GENERATOR WITH
10 SEMICONDUCTOR PROCESSING CHAMBER." This application is related to and co-assigned U.S. Patent No. 6,830,624 to Janakiraman *et al.*, issued December 14, 2004, and titled "BLOCKER PLATE BY-PASS FOR REMOTE PLASMA CLEAN." This application is also related to co-assigned U.S. Patent No. 5,558,717 to Zhao *et al.*, and titled "CVD PROCESSING CHAMBER." The entire contents of all related
15 applications is hereby incorporated by reference for all purposes.

BACKGROUND OF THE INVENTION

[0002] Semiconductor device geometries have dramatically decreased in size since their introduction several decades ago. Modern semiconductor fabrication equipment routinely produces devices with 250nm, 180nm, and 65nm feature sizes,
20 and new equipment is being developed and implemented to make devices with even smaller geometries. The smaller sizes, however, mean device elements have to work closer together which can increase the chances of electrical interference, including cross-talk and parasitic capacitance.

[0003] To reduce the degree of electrical interference, dielectric insulating materials
25 are used to fill the gaps, trenches, and other spaces between the device elements, metal lines, and other device features. The dielectric materials are chosen for their

ease of formation in the spaces between device features, and their low dielectric constants (i.e., "k-values"). Dielectrics with lower k-values are better at minimizing cross-talk and RC time delays, as well as reducing the overall power consumption of the device. Conventional dielectric materials include silicon oxide, which has an
5 average k-value between 4.0 and 4.2 when deposited with conventional CVD techniques.

[0004] While the k-value of conventional CVD silicon oxide is acceptable for many device structures, the ever decreasing sizes and increasing densities of device elements have kept semiconductor manufacturers looking for dielectric materials
10 with lower k-values. One approach has been to dope the silicon oxide with fluorine to make a fluorine-doped silicon oxide film (i.e., "FSG" film) with a dielectric constant as low as about 3.4 to 3.6. Another has been the development of spin-on glass techniques that coat the substrate with highly flowable precursors like hydrogen silsesquioxane (HSQ) to form a porous low-k film.

15 [0005] More recently, silicon-oxygen-carbon (Si-O-C) films have been developed with k-values of 3.0 or less. These low-k films are often deposited by the chemical vapor deposition of carbon-silicon and oxygen precursors on the substrate. While these Si-O-C films have lower k-values than pure and fluorine-doped silicon oxide films, they also tend to be substantially more porous, which can have negative
20 consequences. Porous films are prone to increased absorption of water, which can increase the k-value of the film. Porous films also have higher "wet etch rate ratios" (WERRs) that can make the film more prone to corrosion and stress cracking. Thus, there is a need for new methods of depositing low-k carbon based films with reduced porosity, lower WERR values, and less cracking. These and other issues are
25 addressed by embodiments of the invention.

BRIEF SUMMARY OF THE INVENTION

[0006] Embodiments of the invention may also include a method for depositing a silicon oxide layer over a substrate. The method includes providing a substrate to a deposition chamber. A first silicon-containing precursor, a second silicon-

containing precursor and a NH_3 plasma is reacted to form a silicon oxide layer. The first silicon-containing precursor includes at least one of Si-H bond and Si-Si bond. The second silicon-containing precursor includes at least one Si-N bond. The deposited silicon oxide layer is annealed.

5 [0007] Embodiments of the invention include methods of depositing a silicon oxide layer over a substrate. The methods may include providing a substrate to a deposition chamber. An atomic oxygen precursor may be generated outside the deposition chamber and introduced into the chamber. A silicon precursor may be introduced to the deposition chamber. The silicon precursor may have a C:Si atom
10 ratio of about 8 or less. The silicon precursor and the atomic oxygen precursor may be first mixed in the chamber. The silicon precursor and the atomic oxygen precursor may be reacted to form the silicon oxide layer on the substrate. The deposited silicon oxide layer may be annealed.

[0008] Embodiments of the invention may also include methods of depositing a
15 silicon oxide layer over a substrate. The methods may include providing a substrate to a deposition chamber. An atomic oxygen precursor may be generated by plasmaizing an ozone-containing precursor outside the deposition chamber and introduced into the chamber. A silicon precursor may be introduced to the deposition chamber. The silicon precursor may have a C:Si atom ratio of about 8 or
20 less. The silicon precursor and the atomic oxygen precursor may be first mixed in the chamber. The silicon precursor and the atomic oxygen precursor may be reacted at a process pressure between about 100 Torr and about 760 Torr to form the silicon oxide layer on the substrate. The deposited silicon oxide layer may be annealed.

[0009] Additional embodiments and features are set forth in part in the description
25 that follows, and in part will become apparent to those skilled in the art upon examination of the specification or may be learned by the practice of the invention. The features and advantages of the invention may be realized and attained by means of the instrumentalities, combinations, and methods described in the specification.

BRIEF DESCRIPTION OF THE DRAWINGS

[0010] A further understanding of the nature and advantages of the present invention may be realized by reference to the remaining portions of the specification and the drawings wherein like reference numerals are used throughout the several drawings to refer to similar components. In some instances, a sublabel is associated with a reference numeral and follows a hyphen to denote one of multiple similar components. When reference is made to a reference numeral without specification to an existing sublabel, it is intended to refer to all such multiple similar components.

[0011] FIG. 1 shows a flowchart that includes steps in an exemplary method 100 of forming an oxide layers over a substrate.

[0012] FIGS. 2A-2D are schematic cross-sectional views showing an exemplary method for forming a silicon oxide layer over a substrate.

[0013] FIG. 3 is a flow chart showing another exemplary embodiment for forming a silicon oxide layer.

[0014] FIG. 4A shows a vertical cross-sectional view of an exemplary thin film deposition system.

[0015] FIG. 4B is a simplified diagram of an exemplary system monitor/controller component of a thin film deposition system.

DETAILED DESCRIPTION OF THE INVENTION

[0016] Systems and methods are described for depositing a silicon oxide layer with desired flowability that is then annealed (*i.e.*, cured) into an oxide layer or fill having a desired quality. The desired flowability of the initially formed oxide allows it to fill aspect ratio gaps and trenches (*e.g.*, aspect ratios greater than 5:1) without gaps or seams. The annealing step then drives out moisture to leave behind a dense oxide film having a wet etch rate ratio (WERR) that may approach the practical limit for silicon oxide films (*e.g.*, WERRs down to about 1.8 to about 1.4).

[0017] The exemplary methods may include the remote generation of reactive atomic oxygen outside a deposition/reaction chamber. The atomic oxygen may be first mixed with a silicon precursor having a C:Si atom ratio of about 8 or less in the deposition chamber, where they can react even at low temperatures and pressures and deposit silicon oxide over a substrate. The oxide formed may have a desired level of hydroxyl groups bonded to the silicon, which can make the oxide desirably flowable. Once deposited, the oxide will desirably flow even at low temperatures to fill nascent voids and seams during a gap or trench fill. Then after the deposition, the annealing step may convert an amount of the Si-OH groups into silicon dioxide and water vapor, which is driven out of the deposited film.

Exemplary Oxide Layer Formation Processes

[0018] FIG. 1 shows a flowchart that includes steps in an exemplary method 100 of forming an oxide layers over a substrate. The method 100 can include providing a substrate 200 to a deposition chamber in step 102. The substrate 200 may be a silicon substrate, a III-V compound substrate, a silicon/germanium (SiGe) substrate, an epi-substrate, a silicon-on-insulator (SOI) substrate, a display substrate such as a liquid crystal display (LCD), a plasma display, an electro luminescence (EL) lamp display, or a light emitting diode (LED) substrate, for example. In some embodiments, the substrate 200 may include at least one structure, such as trench structure, well, junction, diode, transistor, metal-oxide-semiconductor field effect transistor (MOSFET), interlayer dielectric (ILD) structure, inter-metal dielectric (IMD) structure, circuit, other semiconductor structure or various combinations thereof. The substrate 200 may be a semiconductor wafer (e.g., a 200 mm, 300 mm, 400 mm, etc. silicon wafer). In some embodiments, the substrate 200 may have at least one trench such as trenches 210 formed therein as shown in FIG. 2A. In some embodiments, the substrate 200 may be a semiconductor wafer (e.g., a 200 mm, 300 mm, 400 mm, etc. silicon wafer) and may include structures, device components, etc., formed in earlier processes. For example, the substrate may include the trenches 210 with high height to width aspect ratios (e.g., an aspect ratio of 5:1 or more, 6:1 or

more, 7:1 or more, 8:1 or more, 9:1 or more, 10:1 or more, 11:1 or more, 12:1 more, etc.).

[0019] In some embodiments, the method 100 may include the remote generation of an atomic oxygen precursor at a location outside the deposition chamber in step

5 104. The atomic oxygen precursor may be generated by the dissociation of an oxygen containing precursor such as molecular oxygen (O₂), ozone (O₃), an nitrogen-oxygen compound (*e.g.*, NO, NO₂, N₂O, *etc.*), a hydrogen-oxygen compound (*e.g.*, H₂O, H₂O₂, *etc.*), a carbon-oxygen compound (*e.g.*, CO, CO₂, *etc.*), as well as other oxygen containing precursors and combinations of precursors.

10 [0020] In some embodiments, the atomic oxygen precursor may be generated by the dissociation of an ozone-containing precursor. The ozone-containing precursor may be a mixture gas of oxygen and ozone. For example, oxygen can be provided into an ozone generator. Within the ozone generator, at least a portion of oxygen can be ozonized as ozone. In some embodiments, the oxygen may have a flow rate
15 between about 3 standard liters per minute (slm) and about 20 slm. After the ozonization, ozone within oxygen may have a weight percentage between about 6% and about 20%.

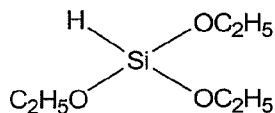
[0021] In some embodiments, the dissociation of the oxygen containing precursor to generate the atomic oxygen may be done by thermal dissociation, ultraviolet light
20 dissociation, and/or plasma dissociation, among other methods. Plasma dissociation may involve striking a plasma from helium, argon, *etc.*, in a remote plasma generating chamber and introducing the oxygen precursor to the plasma to generate the atomic oxygen precursor.

[0022] The atomic oxygen precursor can be introduced to the deposition chamber
25 in step 106 where it may mix for the first time with a silicon precursor, which can be introduced to the chamber in step 108. The atomic oxygen precursor can react with the silicon precursor (and other deposition precursors that may be present in the reaction chamber) at a temperature between about -10°C and about 200°C and a pressure between about 10 Torr and about 760 Torr total chamber pressure to form a

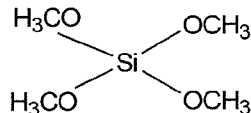
silicon oxide film 220 (shown in FIG. 2B) in step 110. The silicon oxide film 220 can reduce the aspect ratio of the trenches 210 to that of trenches 210a.

[0023] The silicon precursor may have a C:Si atom ratio of about 8 or less (*e.g.*, a C:Si ratio of 7, 6, 5, 4, 3, 2, 1 or less). This means there can be fewer than 8 carbon atoms in the silicon precursor molecule for every silicon atom present.

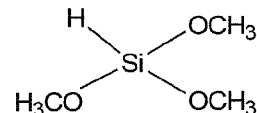
[0024] In some embodiments, the silicon precursor may be a siloxane compound such as triethoxysiloxane (TRIES), tetramethoxysiloxane (TMOS), trimethoxysiloxane (TRIMOS), hexamethoxydisiloxane (HMODS), octamethoxytrisiloxane (OMOTS), and/or octamethoxydodecasiloxane (OMODDS), among other siloxane compounds:



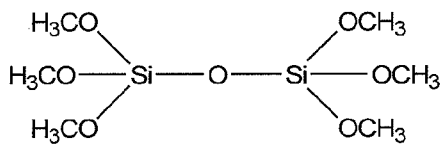
Triethoxysiloxane
(TRIES)



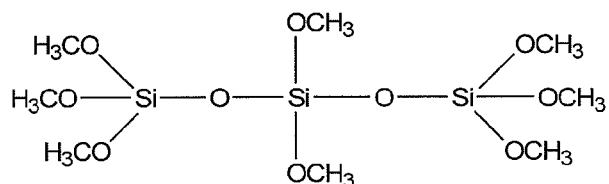
Tetramethoxysiloxane
(TMOS)



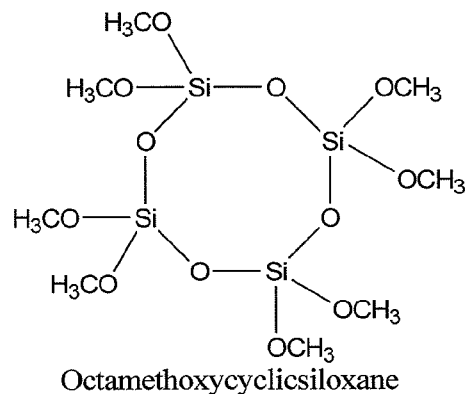
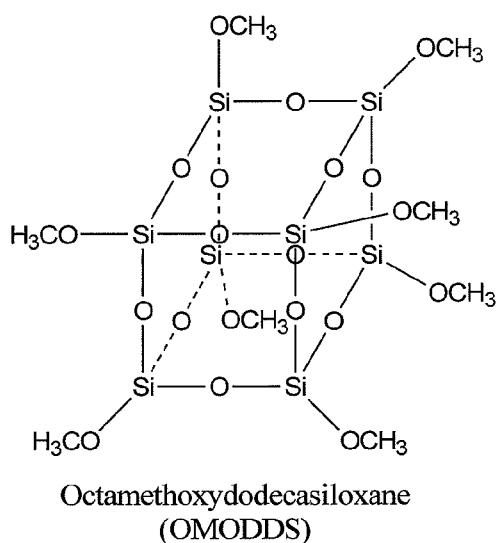
Trimethoxysiloxane
(TRIMOS)



Hexamethoxydisiloxane
(HMODS)

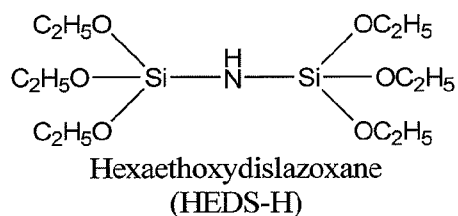
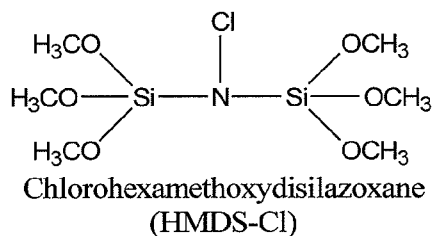
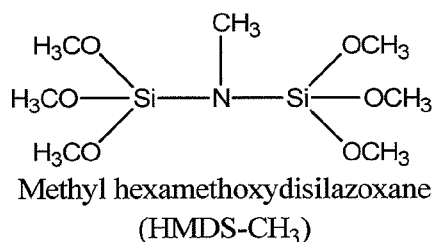
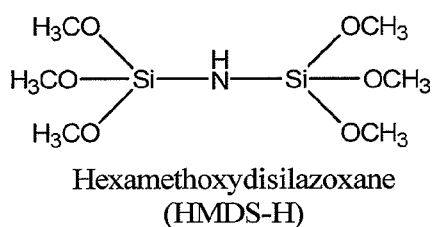


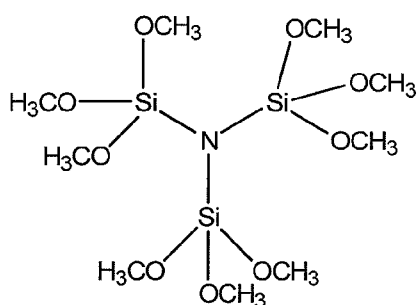
Octamethoxytrisiloxane
(OMOTS)



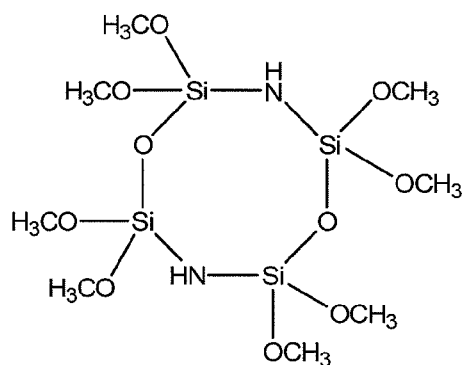
[0025] In other embodiments, the silicon precursor may also be a silazoxane compound that includes one or more nitrogen groups. The silazoxane compounds may include hexamethoxydisilazoxane (HMDS-H), methyl

- 5 hexamethoxydisilazoxane (HMDS-CH₃), chlorohexamethoxydisilazoxane (HMDS-Cl), hexaethoxydisilazoxane (HEDS-H), nonamethoxytrisilazoxane (NMTS), and octamethoxycyclisilazoxane (OMCS), among other silazoxane compounds:



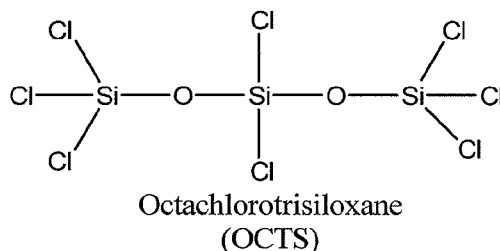
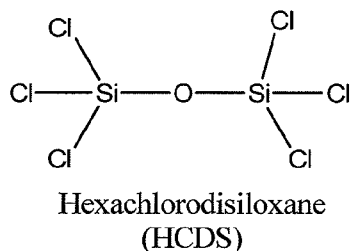
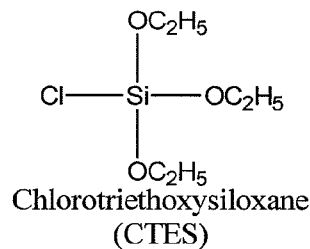
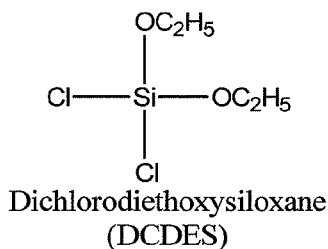
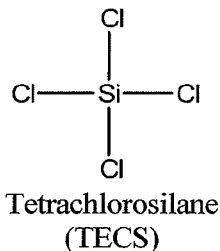


Nonamethoxytrisilazoxane
(NMTS)



Octamethoxycyclicsilazoxane
(OMCS)

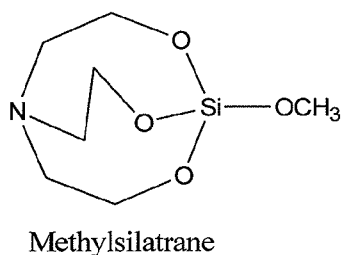
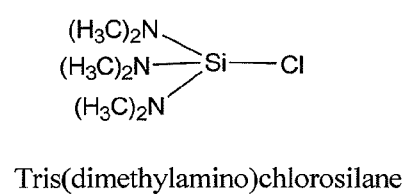
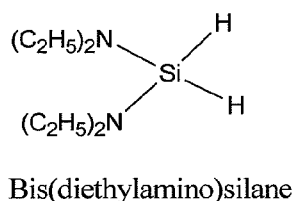
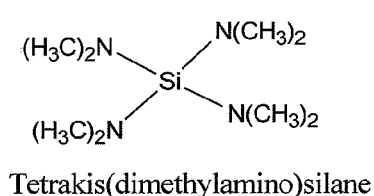
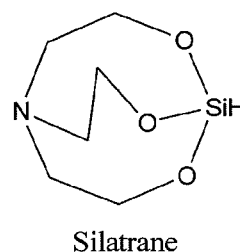
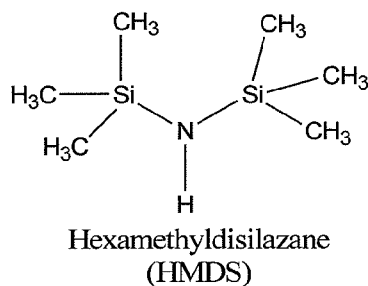
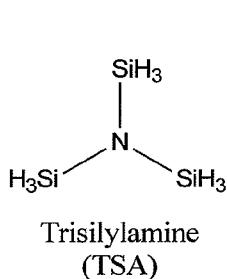
[0026] In still other embodiments, the silicon precursor may be a halogenated siloxane compound that includes one or more halogen groups (*e.g.*, fluoride, chloride, bromide, or iodide groups). For example, the halogenated siloxane may be a chlorinated siloxane compound such as tetrachlorosilane (TECS), dichlorodiethoxysiloxane (DCDES), chlorotriethoxysiloxane (CTES), hexachlorodisiloxane (HCDS), and/or octachlorotrisiloxane (OCTS), among other chlorinated siloxane compounds:



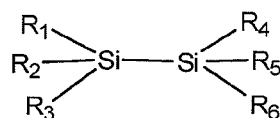
[0027] The silicon precursor may have an O:Si ratio of about 0, 0.5, 1, 2, 3, 4, 5, 6, *etc.*, or more. For example, TMOS has an O:Si atom ratio of about 4. Other silicon precursors, such as TRIES, and TRIMOS, have an O:Si ratio of about 3. Still others, such as HCDS have an O:Si ratio of 0.5, and TECS has an O:Si ratio of 0.

[0028] The silicon precursors may include an Si-O-Si linkage, as seen in HMODS, OMOTS, OMODDS, HCDS, and OCTS, among other organo-silicon compounds. This linkage in the silicon precursor may facilitate the formation of SiO_x films with reduced contamination from carbon and hydroxyl groups.

- 5 [0029] In some embodiments, the silicon precursors may include aminosilanes such as Trisilylamine (TSA), Hexamethyldisilazane (HMDS), Silatrane, Tetrakis(dimethylamino)silane, Bis(diethylamino)silane, Bis-tert-butylaminosilane; Bis-dimethylaminosilane (BDMAS), Tris(dimethylamino)chlorosilane, and methylsilatrane, among other compounds:

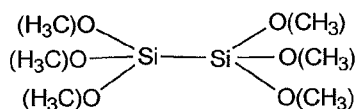


[0030] In other embodiments, the silicon precursors may include disilanes including, alkoxy disilanes, alkoxy-alkyl disilanes, and alkoxy-acetoxy disilanes. The alkoxy disilanes may include:

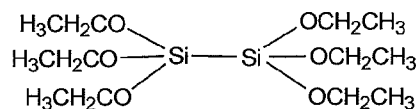


wherein R_{1-6} may be, independently, a C_{1-3} alkyloxy group. For example, the alkoxy disilanes may include hexamethoxydisilane, and hexaethoxydisilane among other alkoxy disilanes.

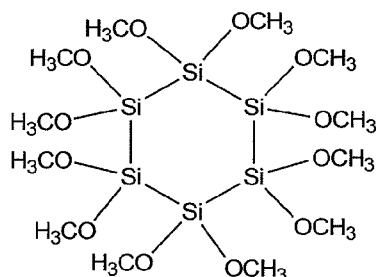
- 5 [0031] The alkoxy disilanes may include cyclic disilane compounds with alkoxy groups bonded to the Si moieties. For example, the alkoxy cyclosilanes may include octaethoxycyclobutasilane, decabutoxycyclopentasilane, and dodecamethoxycyclohexasilane, among others. Some examples of alkoxy disilanes are shown below:



Hexamethoxydisilane



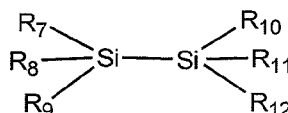
Hexaethoxydisilane



Dodecamethoxycyclohexasilane

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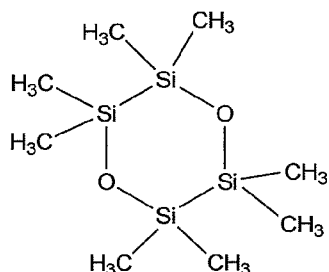
- [0032] The alkoxy-alkyl disilanes may include:



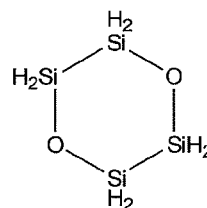
wherein R_{7-12} may be, independently, a C_{1-3} alkyl group or a C_{1-3} alkyloxy group, and wherein at least one of R_{7-12} is a alkyl group and at least one of R_{7-12} is an alkyloxy group. Alkoxy-alkyl disilanes may also include cyclic disilanes with alkyl and alkoxy moieties, such as butasilanes, pentasilanes, hexasilanes, heptasilane, octasilanes, *etc.*, having at least one alkyl and alkoxy group bonded thereto. Examples include octamethyl-1,4-dioxa-2,3,5,6-tetrasilacyclohexane; 1,4-dioxa-

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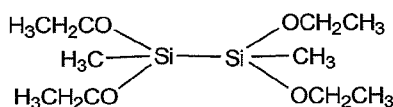
2,3,5,6-tetrasilacyclohexane; and 1,2,3,4,5,6-hexamethoxy-1,2,3,4,5,6-hexamethylcyclohexasilane, among other alkoxy-alkyl cyclosilanes. Some examples of alkoxy-alkyl disilanes are shown below:



octamethyl-1,4-dioxo-2,3,5,6-tetrasilacyclohexane

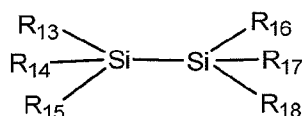


1,4-dioxo-2,3,5,6-tetrasilacyclohexane



1,1,2,2-tetraethoxy-1,2-dimethyldisilane

5 [0033] Alkoxy-acetoxy disilanes may include:



wherein R_{13-17} may be, independently, a C_{1-3} alkyl group, a C_{1-3} alkoxy group, or an acetoxy group, and wherein at least one of R_{13-17} is an alkoxy group and at least one of R_{13-17} is an acetoxy group.

10 [0034] In still other embodiments, the silicon precursors may include organocyclosilanes such as cyclobutasilane, cyclopentasilane, cyclohexasilane, cycloheptasilane, cyclooctasilane, *etc.*

[0035] In some embodiments, the silicon precursor may be mixed with a carrier gas before or during its introduction to the deposition chamber. A carrier gas may be an
 15 inactive gas that does not substantially interfere with the formation of the oxide film 210 over the substrate 200. Examples of carrier gases can include helium, neon, argon, and hydrogen (H_2), among other gases.

[0036] In embodiments of method 100, the atomic oxygen precursors and silicon precursors may not be mixed before being introduced to the deposition chamber.

The precursors may enter the chamber through separate spatially separated precursor inlets distributed around reaction chamber. For example, the atomic oxygen precursor may enter from an inlet (or inlets) at the top of the chamber and positioned directly above the substrate. The inlet may direct the flow of the oxygen precursor in a direction substantially perpendicular to the substrate deposition surface. Meanwhile, the silicon precursor may enter from one or more inlets around the sides of the deposition chamber. The inlets may direct the flow of the silicon precursor in a direction approximately parallel to the deposition surface.

[0037] In some embodiments, the atomic oxygen precursors and silicon precursors can be sent through separate ports of a multi-port showerhead. For example, a showerhead positioned above the substrate may include a pattern of openings for the precursors to enter the deposition chamber. One subset of openings may be supplied by the atomic oxygen precursor, while a second subset of openings is supplied by the silicon precursor. Precursors traveling through different sets of opening may be fluidly isolated from each other until exiting into the deposition chamber. Additional details about types and designs of precursor handling equipment is described in a co-assigned U.S. Provisional Patent App. No. 60/803,499 to Lubomirsky *et al*, filed May 30, 2006, and titled "PROCESS CHAMBER FOR DIELECTRIC GAPFILL," the entire contents of which are hereby incorporated by reference for all purposes.

[0038] As the atomic oxygen precursors and silicon precursors may react in the deposition chamber, they can form the silicon oxide layer 210 over the substrate deposition surface in step 110. The initial oxide layer may have desired flowability, and can desirably migrate into gaps, trenches, voids, seams, *etc.*, in the structures present at the deposition surface. This can allow the method 100 to provide oxide fills that can be substantially free of voids and seams in gaps, trenches, and other surface structures that have high height to width aspect ratios (*e.g.*, ARs of about 5:1, 6:1, 6:1, 8:1, 9:1, 10:1, 11:1, and 12:1 or more).

[0039] Referring again to FIG. 1, a post deposition anneal 112 of the deposited silicon oxide layer 210 (shown in FIG. 2B) may be done in a single step, or multiple

steps. A single step anneal may be done, for example, by heating the deposited layer to about 300°C to about 1000°C (*e.g.*, about 600°C to about 900°C) in a substantially dry atmosphere (*e.g.*, dry nitrogen, helium, argon, *etc.*). The anneal can remove moisture from the deposited layer and converts Si-OH groups into silicon oxide.

- 5 The annealed silicon oxide layer may have improved film quality (*e.g.*, a WERR of about 6 to about 3, or less) and improved qualities as a dielectric (*e.g.*, a k-value approaching or equal to pure silicon dioxide). In some embodiments, the anneal step 112 may be carried out at about 900°C in a nitrogen ambient for about one hour.

[0040] In some embodiments, multi-step anneals may include a two-step anneal
10 where the layer first can undergo a wet anneal stage, such as heating the layer to, for example, about 650°C in the presence of steam. This may be followed by a dry anneal stage, where the layer can be heated to a higher temperature (*e.g.*, about 900°C) in an atmosphere that is substantially free of moisture (*e.g.*, dry N₂).

[0041] In addition to wet and dry thermal annealing, other annealing techniques
15 (alone or in combination) may be used to anneal the silicon oxide layer 114. These include a steam anneal, a thermal anneal, an inductively coupled plasma (ICP) anneal, an ultraviolet light anneal, an e-beam anneal, an acid vapor catalysis anneal, a base vapor catalysis anneal and/or a microwave anneal, among others.

[0042] FIG. 2D is a cross-sectional view showing an exemplary STI structure. In
20 FIG. 2D, a dielectric layer 230 such as a high density plasma chemical vapor deposition (HDP CVD) layer may be formed over the annealed silicon oxide layer 220a. Since the annealed silicon oxide layer 220a can have a thickness at the bottom region of the trenches 210 larger than that on the sidewalls of the trenches 210, the aspect ratio of the trenches 210a may be desirably reduced. Accordingly, the
25 dielectric layer 230 may be formed and filled within the trenches 210a without substantially forming seams, gaps or voids within the dielectric layer 230. In some embodiments, the formation of the dielectric layer 230 can be optional if the oxide layer 220 may desirably fill the trenches 210 shown in FIG. 2A.

[0043] In some embodiments, the dielectric layer 230 may be subjected to a thermal
30 treatment such as an anneal process (not shown). The thermal treatment may

desirably densify the dielectric layer 230. In some embodiments, the processes for forming the dielectric layer 230 and the thermal treatment may be optional. The silicon oxide layer 220 (shown in FIG. 2B) may be formed and substantially fill the trenches 210.

5 Another Exemplary Oxide Layer Formation Processes

[0044] FIG. 3 is a flow chart showing another exemplary method for forming an silicon oxide layer. Referring to FIG. 3, the method 300 for forming an silicon oxide layer may include steps 302, 304 and 306. Step 302 can provide a substrate (not shown) into a deposition chamber. The substrate may be similar to the substrate 200
10 described above in conjunction with FIG. 1.

[0045] In step 304, a first silicon-containing precursor, a second silicon-containing precursor and an ammonia (NH_3) plasma can be reacted to form a silicon oxide layer. In some embodiments, the first silicon-containing precursor can include at least one of Si-H bond and Si-Si bond. In other embodiments, the first-silicon-
15 containing precursor can be reactive with NH_3 plasma. In still other embodiments, the first silicon-containing precursor may include at least one of TMDSO, trimethosylsiloxane (TRIMOS), hexachlorodisiloxane (HCDS), DMTMDS, SAM24, TMCTS and BTBAS. In some embodiments, the first silicon-containing precursor may have a C:Si atom ratio of about 8 or less.

[0046] In some embodiments, the second silicon-containing precursor may include at least one Si-N bond. The second silicon-containing precursor may desirably reduce shrinkage of the silicon oxide layer. In some embodiments, the second silicon-containing precursor may expand the atomic structure of the silicon oxide layer. For example, the shrinkage of the silicon oxide layer can be of about 32% or
25 less. In some embodiments, the second silicon-containing precursor may expand the silicon oxide layer by 11% or less.

[0047] In some embodiments, the second-containing precursor may include TSA. In some embodiments, at least one of Si-H bonds of TSA can be replaced by Si- CH_3 bond. For example, a Si-H bond on each of SiH_3 can be replaced by a Si- CH_3 bond.

[0048] It is noted that the NH_3 plasma may be generated in an external plasma generator or in the deposition chamber. The first silicon-containing precursor and the second silicon-containing precursor may be mixed or separately introduced into the deposition chamber to interact with the NH_3 plasma.

5 [0049] In some embodiments using TMDSO and TSA, step 304 may have a processing temperature between about 0 °C or more. In some embodiments, the processing temperature is between about 10 °C and about 25 °C. The flow rate of TSA can be between about 10 standard centimeter per minute (sccm) and about 550 sccm. In some embodiments, the flow rate of TSA can be between about 400 sccm
10 and about 430 sccm. The flow rate of TMDSO can be between about 10 milligrams per minute (mgm) and about 1500 mgm. In some embodiments, the flow rate of TMDSO is about 1000 mgm. In some embodiments, the precursor for generating the NH_3 plasma can have a flow rate between about 1000 sccm and about 1,250 sccm. In some embodiments, the flow rate of NH_3 is between about 1,000 sccm and about
15 1,250 sccm.

[0050] Referring again to FIG. 3, step 306 can cure the deposited silicon oxide layer. In some embodiments, step 306 may be similar to step 112 described above in conjunction with FIG. 1.

[0051] In some embodiments for forming a silicon oxide layer, the flow rate of TSA
20 can be about 400 sccm. The flow rate of TMDSO can be about 1,000 mgm. The flow rate of the precursor for generating the NH_3 plasma can be about 1,250 sccm. The processing temperature can be about 10°C. The processing pressure can be about 1.5 Torr. In some embodiments, the curing step 306 may be omitted. An anneal process (not shown) may be applied to the deposited silicon oxide layer, the anneal process
25 may be a two-step steam anneal. One of the steps may have a processing temperature of about 600°C; the other of the steps may have a processing temperature of about 850°C.

Exemplary Substrate Processing System

[0052] Deposition systems that may implement embodiments of the present invention may include high-density plasma chemical vapor deposition (HDP-CVD) systems, plasma enhanced chemical vapor deposition (PECVD) systems, sub-atmospheric chemical vapor deposition (SACVD) systems, and thermal chemical vapor deposition systems, among other types of systems. Specific examples of CVD systems that may implement embodiments of the invention include the CENTURA ULTIMA™ HDP-CVD chambers/systems, and PRODUCER™ PECVD chambers/systems, available from Applied Materials, Inc. of Santa Clara, California.

[0053] Examples of substrate processing systems that can be used with exemplary methods of the invention may include those shown and described in co-assigned U.S. Provisional Patent App. No. 60/803,499 to Lubomirsky *et al*, filed May 30, 2006, and titled "PROCESS CHAMBER FOR DIELECTRIC GAPFILL," the entire contents of which is herein incorporated by reference for all purposes. Additional exemplary systems may include those shown and described in U.S. Pat. Nos. 6,387,207 and 6,830,624, which are also incorporated herein by reference for all purposes.

[0054] Referring now to FIG. 4A, vertical cross-sectional views of a CVD system 10 is shown that has a vacuum or processing chamber 15 that includes a chamber wall 15a and a chamber lid assembly 15b. The CVD system 10 contains a gas distribution manifold 11 for dispersing process gases to a substrate (not shown) that rests on a heated pedestal 12 centered within the process chamber 15. Gas distribution manifold 11 may be formed from an electrically conducting material in order to serve as an electrode for forming a capacitive plasma. During processing, the substrate (*e.g.* a semiconductor wafer) is positioned on a flat (or slightly convex) surface 12a of the pedestal 12. The pedestal 12 can be moved controllably between a lower loading/off-loading position (depicted in FIG. 4A) and an upper processing position (indicated by dashed line 14 in FIG. 4A), which is closely adjacent to the manifold 11. A centerboard (not shown) includes sensors for providing information on the position of the wafers.

[0055] Deposition and carrier gases are introduced into the chamber 15 through perforated holes 13b of a conventional flat, circular gas distribution faceplate 13a.

More specifically, deposition process gases flow into the chamber through the inlet manifold 11, through a conventional perforated blocker plate 42 and then through holes 13b in gas distribution faceplate 13a.

[0056] Before reaching the manifold 11, deposition and carrier gases are input from gas sources 7 through gas supply lines 8 into a mixing system 9 where they are combined and then sent to manifold 11. Generally, the supply line for each process gas includes (i) several safety shut-off valves (not shown) that can be used to automatically or manually shut-off the flow of process gas into the chamber, and (ii) mass flow controllers (also not shown) that measure the flow of gas through the supply line. When toxic gases are used in the process, the several safety shut-off valves are positioned on each gas supply line in conventional configurations.

[0057] The deposition process performed in the CVD system 10 can be either a thermal process or a plasma-enhanced process. In a plasma-enhanced process, an RF power supply 44 applies electrical power between the gas distribution faceplate 13a and the pedestal 12 so as to excite the process gas mixture to form a plasma within the cylindrical region between the faceplate 13a and the pedestal 12. (This region will be referred to herein as the "reaction region"). Constituents of the plasma react to deposit a desired film on the surface of the semiconductor wafer supported on pedestal 12. RF power supply 44 is a mixed frequency RF power supply that typically supplies power at a high RF frequency (RF1) of 13.56 MHz and at a low RF frequency (RF2) of 360 KHz to enhance the decomposition of reactive species introduced into the vacuum chamber 15. In a thermal process, the RF power supply 44 would not be utilized, and the process gas mixture thermally reacts to deposit the desired films on the surface of the semiconductor wafer supported on the pedestal 12, which is resistively heated to provide thermal energy for the reaction.

[0058] During a plasma-enhanced deposition process, the plasma heats the entire process chamber 10, including the walls of the chamber body 15a surrounding the exhaust passageway 23 and the shut-off valve 24. When the plasma is not turned on or during a thermal deposition process, a hot liquid is circulated through the walls 15a of the process chamber 15 to maintain the chamber at an elevated temperature.

The passages in the remainder of the chamber walls 15a are not shown. Fluids used to heat the chamber walls 15a include the typical fluid types, *i.e.*, water-based ethylene glycol or oil-based thermal transfer fluids. This heating (referred to as heating by the "heat exchanger") beneficially reduces or eliminates condensation of undesirable reactant products and improves the elimination of volatile products of the process gases and other contaminants that might contaminate the process if they were to condense on the walls of cool vacuum passages and migrate back into the processing chamber during periods of no gas flow.

[0059] The remainder of the gas mixture that is not deposited in a layer, including reaction byproducts, is evacuated from the chamber 15 by a vacuum pump (not shown). Specifically, the gases are exhausted through an annular, slot-shaped orifice 16 surrounding the reaction region and into an annular exhaust plenum 17. The annular slot 16 and the plenum 17 are defined by the gap between the top of the chamber's cylindrical side wall 15a (including the upper dielectric lining 19 on the wall) and the bottom of the circular chamber lid 20. The 360.degree. circular symmetry and uniformity of the slot orifice 16 and the plenum 17 are important to achieving a uniform flow of process gases over the wafer so as to deposit a uniform film on the wafer.

[0060] From the exhaust plenum 17, the gases flow underneath a lateral extension portion 21 of the exhaust plenum 17, past a viewing port (not shown), through a downward-extending gas passage 23, past a vacuum shut-off valve 24 (whose body is integrated with the lower chamber wall 15a), and into the exhaust outlet 25 that connects to the external vacuum pump (not shown) through a foreline (also not shown).

[0061] The wafer support platter of the pedestal 12 (preferably aluminum, ceramic, or a combination thereof) is resistively heated using an embedded single-loop embedded heater element configured to make two full turns in the form of parallel concentric circles. An outer portion of the heater element runs adjacent to a perimeter of the support platter, while an inner portion runs on the path of a

concentric circle having a smaller radius. The wiring to the heater element passes through the stem of the pedestal 12.

[0062] Typically, any or all of the chamber lining, gas inlet manifold faceplate, and various other reactor hardware are made out of material such as aluminum, anodized aluminum, or ceramic. An example of such a CVD apparatus is described in co-assigned U.S. Pat. No. 5,558,717 entitled "CVD Processing Chamber," issued to Zhao *et al*, and hereby incorporated by reference in its entirety.

[0063] A lift mechanism and motor 32 (FIG. 4A) raises and lowers the heater pedestal assembly 12 and its wafer lift pins 12b as wafers are transferred into and out of the body of the chamber 15 by a robot blade (not shown) through an insertion/removal opening 26 in the side of the chamber 10. The motor 32 raises and lowers pedestal 12 between a processing position 14 and a lower, wafer-loading position. The motor, valves or flow controllers connected to the supply lines 8, gas delivery system, throttle valve, RF power supply 44, and chamber and substrate heating systems are all controlled by a system controller over control lines 36, of which only some are shown. Controller 34 relies on feedback from optical sensors to determine the position of movable mechanical assemblies such as the throttle valve and susceptor which are moved by appropriate motors under the control of controller 34.

[0064] In the exemplary embodiment, the system controller includes a hard disk drive (memory 38), a floppy disk drive and a processor 37. The processor contains a single-board computer (SBC), analog and digital input/output boards, interface boards and stepper motor controller boards. Various parts of CVD system 10 conform to the Versa Modular European (VME) standard which defines board, card cage, and connector dimensions and types. The VME standard also defines the bus structure as having a 16-bit data bus and a 24-bit address bus.

[0065] System controller 34 controls all of the activities of the CVD machine. The system controller executes system control software, which is a computer program stored in a computer-readable medium such as a memory 38. Preferably, the memory 38 is a hard disk drive, but the memory 38 may also be other kinds of memory. The computer program includes sets of instructions that dictate the timing,

mixture of gases, chamber pressure, chamber temperature, RF power levels, susceptor position, and other parameters of a particular process. Other computer programs stored on other memory devices including, for example, a floppy disk or other another appropriate drive, may also be used to operate controller 34.

5 [0066] A process for depositing a film on a substrate or a process for cleaning the chamber 15 can be implemented using a computer program product that is executed by the controller 34. The computer program code can be written in any conventional computer readable programming language: for example, 68000 assembly language, C, C++, Pascal, Fortran or others. Suitable program code is entered into a single file, 10 or multiple files, using a conventional text editor, and stored or embodied in a computer usable medium, such as a memory system of the computer. If the entered code text is in a high level language, the code is compiled, and the resultant compiler code is then linked with an object code of precompiled Microsoft Windows® library routines. To execute the linked, compiled object code the system user invokes the 15 object code, causing the computer system to load the code in memory. The CPU then reads and executes the code to perform the tasks identified in the program.

[0067] The interface between a user and the controller 34 is via a CRT monitor 50a and light pen 50b, shown in FIG. 4B, which is a simplified diagram of the system monitor and CVD system 10 in a substrate processing system, which may include 20 one or more chambers. In the preferred embodiment two monitors 50a are used, one mounted in the clean room wall for the operators and the other behind the wall for the service technicians. The monitors 50a simultaneously display the same information, but only one light pen 50b is enabled. A light sensor in the tip of light pen 50b detects light emitted by CRT display. To select a particular screen or 25 function, the operator touches a designated area of the display screen and pushes the button on the pen 50b. The touched area changes its highlighted color, or a new menu or screen is displayed, confirming communication between the light pen and the display screen. Other devices, such as a keyboard, mouse, or other pointing or communication device, may be used instead of or in addition to light pen 50b to 30 allow the user to communicate with controller 34.

[0068] FIG. 4A shows a remote plasma generator 60 mounted on the lid assembly 15b of the process chamber 15 including the gas distribution faceplate 13a and the gas distribution manifold 11. A mounting adaptor 64 mounts the remote plasma generator 60 on the lid assembly 15b, as best seen in FIG. 4A. The adaptor 64 is typically made of metal. A mixing device 70 is coupled to the upstream side of the gas distribution manifold 11 (FIG. 4A). The mixing device 70 includes a mixing insert 72 disposed inside a slot 74 of a mixing block for mixing process gases. A ceramic isolator 66 is placed between the mounting adaptor 64 and the mixing device 70 (FIGS. 6A). The ceramic isolator 66 may be made of a ceramic material such as Al_2O_3 (99% purity), Teflon®, or the like. When installed, the mixing device 70 and ceramic isolator 66 may form part of the lid assembly 15b. The isolator 66 isolates the metal adaptor 64 from the mixing device 70 and gas distribution manifold 11 to minimize the potential for a secondary plasma to form in the lid assembly 15b as discussed in more detail below. A three-way valve 77 controls the flow of the process gases to the process chamber 15 either directly or through the remote plasma generator 60.

[0069] The remote plasma generator 60 is desirably a compact, self-contained unit that can be conveniently mounted on the lid assembly 15b and be easily retrofitted onto existing chambers without costly and time-consuming modifications. One suitable unit is the ASTRON® generator available from Applied Science and Technology, Inc. of Woburn, Mass. The ASTRON® generator utilizes a low-field toroidal plasma to dissociate a process gas. In one example, the plasma dissociates a process gas including a fluorine-containing gas such as NF_3 and a carrier gas such as argon to generate free fluorine which is used to clean film deposits in the process chamber 15.

[0070] Having described several embodiments, it will be recognized by those of skill in the art that various modifications, alternative constructions, and equivalents may be used without departing from the spirit of the invention. Additionally, a number of well known processes and elements have not been described in order to

avoid unnecessarily obscuring the present invention. Accordingly, the above description should not be taken as limiting the scope of the invention.

[0071] Where a range of values is provided, it is understood that each intervening value, to the tenth of the unit of the lower limit unless the context clearly dictates

5 otherwise, between the upper and lower limits of that range is also specifically disclosed. Each smaller range between any stated value or intervening value in a stated range and any other stated or intervening value in that stated range is encompassed. The upper and lower limits of these smaller ranges may independently be included or excluded in the range, and each range where either,
10 neither or both limits are included in the smaller ranges is also encompassed within the invention, subject to any specifically excluded limit in the stated range. Where the stated range includes one or both of the limits, ranges excluding either or both of those included limits are also included.

[0072] As used herein and in the appended claims, the singular forms "a", "an", and
15 "the" include plural referents unless the context clearly dictates otherwise. Thus, for example, reference to "a method" includes a plurality of such methods and reference to "the precursor" includes reference to one or more precursors and equivalents thereof known to those skilled in the art, and so forth.

[0073] Also, the words "comprise," "comprising," "include," "including," and
20 "includes" when used in this specification and in the following claims are intended to specify the presence of stated features, integers, components, or steps, but they do not preclude the presence or addition of one or more other features, integers, components, steps, acts, or groups.

WHAT IS CLAIMED IS:

1 1. A method for of depositing a silicon oxide layer on a substrate,
2 the method comprising:
3 providing a substrate to a deposition chamber;
4 reacting a first silicon-containing precursor, a second silicon-containing
5 precursor and a NH₃ plasma to form a silicon oxide layer, the first silicon-containing
6 precursor including at least one of Si-H bond and Si-Si bond, the second silicon-
7 containing precursor including at least one Si-N bond; and
8 annealing the deposited silicon oxide layer.

1 2. The method of claim 1, wherein the first silicon-containing
2 precursor is selected from the group consisting of TMDSO, trimethosysiloxane
3 (TRIMOS), hexachlorodisiloxane (HCDS), DMTMDS, SAM24, TMCTS and BTBAS.

1 3. The method of claim 1, wherein the first silicon-containing
2 precursor is TMDSO.

1 4. The method of claim 1, wherein the first silicon precursor
2 having a C:Si atom ratio of about 8 or less.

1 5. The method of claim 1, wherein the second silicon-containing
2 precursor includes trisilylamine (TSA).

1 6. The method of claim 5, wherein at least one of Si-H bonds of the
2 TSA is replaced by Si-CH₃ bond.

1 7. The method of claim 1, wherein the second silicon-containing
2 precursor is TSA having a flow rate between about 400 sccm and about 430 sccm.

1 8. The method of claim 7, wherein reacting the first silicon-
2 containing precursor, the second silicon-containing precursor and the NH₃ plasma
3 has a processing temperature between about 10 °C and about 25 °C.

1 9. The method of claim 7, wherein reacting the first silicon-
2 containing precursor, the first silicon-containing precursor is TMDSO having a flow
3 rate of about 1,000 mgm.

1 10. The method of claim 7, wherein the NH₃ plasma is generated
2 from a precursor having a flow rate between about 1,200 sccm and about 1,250 sccm.

1 11. The method of claim 7, wherein annealing the deposited silicon
2 oxide layer comprises at least one of a steam anneal, a thermal anneal, an inductively
3 coupled plasma (ICP) anneal, an ultraviolet light anneal, an e-beam anneal, an acid
4 vapor catalysis anneal, a base vapor catalysis anneal and a microwave anneal.

1 12. A method of depositing a silicon oxide layer on a substrate, the
2 method comprising:

3 providing a substrate to a deposition chamber;

4 forming a plasma from a gas mixture comprising a halogen gas;

5 ionizing an ozone-containing precursor by the plasma to form an
6 atomic oxygen precursor, and introducing the atomic oxygen precursor into the
7 chamber;

8 introducing a silicon precursor to the deposition chamber, the silicon
9 precursor having a C:Si atom ratio of about 8 or less, the silicon precursor and the
10 atomic oxygen precursor being first mixed in the chamber;

11 reacting the silicon precursor and the atomic oxygen precursor to form
12 the silicon oxide layer on the substrate; and

13 annealing the deposited silicon oxide layer.

1 13. The method of claim 12, wherein the ozone-containing
2 precursor is a mixture gas of ozone and oxygen, and the ozone has a weight
3 percentage between about 6% and about 20%.

1 14. The method of claim 13, wherein the ozone is generated from
2 the oxygen.

- 1 15. The method of claim 14, wherein a flow rate of the oxygen is
2 between about 3 standard liters per minute (slm) and about 20 slm.
- 1 16. The method of claim 12, wherein a molar ratio of the silicon
2 precursor to the atomic oxygen precursor is between about 1:10 and about 100:1.
- 1 17. The method of claim 12, wherein reacting the silicon precursor
2 and the atomic oxygen precursor has a process pressure between about 100 Torr and
3 about 760 Torr.
- 1 18. The method of claim 12, wherein reacting the silicon precursor
2 and the atomic oxygen precursor has a process temperature between about -10°C
3 and about 200°C.
- 1 19. The method of claim 12, wherein the silicon precursor has an
2 O:Si ratio of about 3 or more.
- 1 20. The method of claim 12, wherein the silicon precursor includes
2 at least one of siloxane, silazoxane and halogenated siloxane.
- 1 21. The method of claim 20, wherein the siloxane is selected from
2 the group consisting of triethoxysiloxane, tetramethoxysiloxane, trimethoxysiloxane,
3 hexamethoxydisiloxane, octamethoxytrisiloxane, octamethoxydodecasiloxane and
4 octamethoxydodecasiloxane.
- 1 22. The method of claim 20, wherein the silazoxane is selected from
2 the group consisting of hexamethoxydisilazoxane, methyl hexamethoxydisilazoxane,
3 chlorohexamethoxydisilazoxane, hexaethoxydisilazoxane,
4 octamethoxycyclicsilazoxane, and nonamethoxytrisilazoxane.
- 1 23. The method of claim 20, wherein the halogenated siloxane is
2 selected from the group consisting of tetrachlorosilane, dichlorodiethoxysiloxane,
3 chlorotriethoxysiloxane, hexachlorodisiloxane, and octachlorotrisiloxane.

1 24. The method of claim 12, wherein the silicon precursor comprises
2 an aminosilane, an alkyl disilane, an alkoxy disilane, an alkoxy-alkyl disilane, an
3 alkoxy-acetoxy disilane, or a cyclosilane.

1 25. The method of claim 24, wherein the amionsilane is selected
2 from the group consisting of trisilylamine (TSA), hexamethyldisilazane (HMDS),
3 silatrane, tetrakis(dimethylamino)silane, bis(diethylamino)silane, bis-tert-
4 butylaminosilane; bis-dimethylaminosilane (BDMAS),
5 sris(dimethylamino)chlorosilane and methylsilatrane.

1 26. The method of claim 12, wherein annealing the deposited silicon
2 oxide layer comprises at least one of a steam anneal, a thermal anneal, an inductively
3 coupled plasma (ICP) anneal, an ultraviolet light anneal, an e-beam anneal, an acid
4 vapor catalysis anneal, a base vapor catalysis anneal and a microwave anneal.

1 27. A method of depositing a silicon oxide layer on a substrate, the
2 method comprising:

3 providing a substrate to a deposition chamber;
4 forming a plasma from a gas mixture comprising a halogen gas;
5 ionizing a precursor including a mixture gas of ozone and oxygen by
6 the plasma to form an atomic oxygen precursor;

7 generating an atomic oxygen precursor by plasmaizing an ozone-
8 containing precursor outside the deposition chamber, and introducing the atomic
9 oxygen precursor into the chamber;

10 introducing a silicon precursor to the deposition chamber, the silicon
11 precursor having a C:Si atom ratio of about 8 or less, the silicon precursor and the
12 atomic oxygen precursor being first mixed in the chamber;

13 reacting the silicon precursor and the atomic oxygen precursor at a
14 process pressure between about 100 Torr and about 760 Torr to form the silicon
15 oxide layer on the substrate; and

16 annealing the deposited silicon oxide layer.

1 28. The method of claim 27, wherein the ozone has a weight
2 percentage between about 6% and about 20%.

1 29. The method of claim 28, wherein a flow rate of the oxygen is
2 between about 3 standard liters per minute (slm) and about 20 slm.

1 30. The method of claim 27, wherein a molar ratio of the silicon
2 precursor to the atomic oxygen precursor is between about 1:10 and about 100:1.

1 31. The method of claim 27, wherein reacting the silicon precursor
2 and the atomic oxygen precursor has a process temperature between about -10°C
3 and about 200°C.

1 32. The method of claim 27, wherein the silicon precursor includes
2 at least one of siloxane, silazoxane and halogenated siloxane.

1 33. The method of claim 32, wherein the siloxane is selected from
2 the group consisting of triethoxysiloxane, tetramethoxysiloxane, trimethoxysiloxane,
3 hexamethoxydisiloxane, octamethoxytrisiloxane, octamethoxydodecasiloxane and
4 octamethoxydodecasiloxane.

1 34. The method of claim 32, wherein the silazoxane is selected from
2 the group consisting of hexamethoxydisilazoxane, methyl hexamethoxydisilazoxane,
3 chlorohexamethoxydisilazoxane, hexaethoxydisilazoxane,
4 octamethoxycyclicsilazoxane, and nonamethoxytrisilazoxane.

1 35. The method of claim 32, wherein the halogenated siloxane is
2 selected from the group consisting of tetrachlorosilane, dichlorodiethoxysiloxane,
3 chlorotriethoxysiloxane, hexachlorodisiloxane, and octachlorotrisiloxane.

1 36. The method of claim 27, wherein the silicon precursor comprises
2 an aminosilane, an alkyl disilane, an alkoxy disilane, an alkoxy-alkyl disilane, an
3 alkoxy-acetoxy disilane, or a cyclosilane.

1 37. The method of claim 27, wherein the amionsilane is selected
2 from the group consisting of trisilylamine (TSA), hexamethyldisilazane (HMDS),
3 silatrane, tetrakis(dimethylamino)silane, bis(diethylamino)silane, bis-tert-
4 butylaminosilane; bis-dimethylaminosilane (BDMAS),
5 sris(dimethylamino)chlorosilane and methylsilatrane.

1 38. The method of claim 27, wherein annealing the deposited silicon
2 oxide layer comprises at least one of a steam anneal, a thermal anneal, an inductively
3 coupled plasma (ICP) anneal, an ultraviolet light anneal, an e-beam anneal, an acid
4 vapor catalysis anneal, a base vapor catalysis anneal and a microwave anneal.